



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



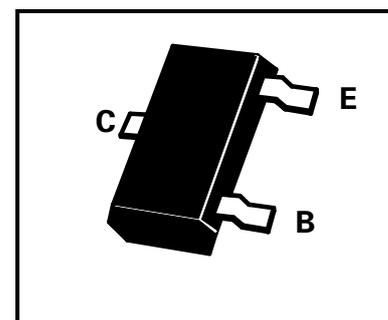
企业QQ二维码

**FEATURES**

 \* Low equivalent on-resistance;  $R_{CE(sat)}$  **250mΩ at 1A**

COMPLEMENTARY TYPE NK-FMMT549 PART

MARKING DETAIL – 449

**ABSOLUTE MAXIMUM RATINGS.**


PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	2	A
Continuous Collector Current	$I_C$	1	A
Base Current	$I_B$	200	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^\circ\text{C}$  unless otherwise stated).**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50		V	$I_C = 1\text{mA}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30		V	$I_C = 10\text{mA}, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E = 100\mu\text{A}, I_C = 0$
Collector Cut-Off Current	$I_{CBO}$		0.1 10	$\mu\text{A}$ $\mu\text{A}$	$V_{CB} = 40\text{V}, I_E = 0$ $V_{CB} = 40\text{V}, T_{amb} = 100^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$		0.1	$\mu\text{A}$	$V_{EB} = 4\text{V}, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.5 1.0	V V	$I_C = 1\text{A}, I_B = 100\text{mA}^*$ $I_C = 2\text{A}, I_B = 200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.25	V	$I_C = 1\text{A}, I_B = 100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.0	V	$I_C = 1\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	70 100 80 40	300		$I_C = 50\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 2\text{A}, V_{CE} = 2\text{V}^*$
Transition Frequency	$f_T$	150		MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{mHz}$
Output Capacitance	$C_{obo}$		15	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

Spice parameter data is available upon request for this device

## TYPICAL CHARACTERISTICS

